# MGSF1N02LT1, MVGSF1N02LT1

# Power MOSFET 750 mAmps, 20 Volts

## N-Channel SOT-23

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc-dc converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

### Features

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- AEC Q101 Qualified MVGSF1N02LT1
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
Drain Current – Continuous @ $T_A = 25^{\circ}C$ – Pulsed Drain Current ( $t_p \le 10 \ \mu s$ )	I <sub>D</sub> I <sub>DM</sub>		
Total Power Dissipation @ $T_A = 25^{\circ}C$	PD	400	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	300	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	ΤL	260	°C

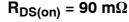
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

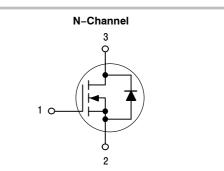


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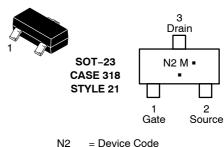
http://onsemi.com

# 750 mAMPS, 20 VOLTS





MARKING DIAGRAM/ PIN ASSIGNMENT



M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location) \*Date Code orientation and overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MGSF1N02LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MVGSF1N02LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

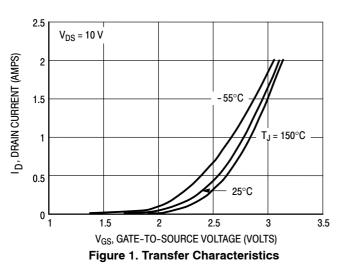
## MGSF1N02LT1, MVGSF1N02LT1

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						•
Drain-to-Source Breakdown Voltage ( $V_{GS} = 0$ Vdc, $I_D = 10 \mu$ Adc)	V <sub>(BR)DSS</sub>	20	-	-	Vdc	
$\label{eq:VDS} \begin{array}{l} \mbox{Zero Gate Voltage Drain Current} \\ (V_{DS} = 20 \mbox{ Vdc}, \mbox{ V}_{GS} = 0 \mbox{ Vdc}) \\ (V_{DS} = 20 \mbox{ Vdc}, \mbox{ V}_{GS} = 0 \mbox{ Vdc}, \mbox{ T}_{J} = \end{array}$	I <sub>DSS</sub>	-		1.0 10	μAdc	
Gate-Body Leakage Current (V <sub>GS</sub>	= $\pm$ 20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	_	-	±100	nAdc
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250 \ \mu Adc$ )	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc	
$ \begin{array}{l} \mbox{Static Drain-to-Source On-Resista} \\ (V_{GS} = 10 \mbox{ Vdc}, \mbox{ I}_{D} = 1.2 \mbox{ Adc}) \\ (V_{GS} = 4.5 \mbox{ Vdc}, \mbox{ I}_{D} = 1.0 \mbox{ Adc}) \end{array} $	r <sub>DS(on)</sub>		0.075 0.115	0.090 0.130	Ω	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>iss</sub>	-	125	-	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>oss</sub>	-	120	-	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 Vdc)	C <sub>rss</sub>	-	45	-	
SWITCHING CHARACTERISTICS (	Note 2)	_			_	
Turn-On Delay Time		t <sub>d(on)</sub>	-	2.5	-	ns
Rise Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 1.0 Adc,	t <sub>r</sub>	-	1.0	-	
Turn-Off Delay Time	R <sub>L</sub> = 50 Ω)	t <sub>d(off)</sub>	-	16	-	
Fall Time		t <sub>f</sub>	-	8.0	-	
Gate Charge (See Figure 6)		Q <sub>T</sub>	-	6000	-	рС
SOURCE-DRAIN DIODE CHARAC	TERISTICS					
Continuous Current	۱ <sub>S</sub>	-	-	0.6	А	
Pulsed Current	I <sub>SM</sub>	_	-	0.75	-	
Forward Voltage (Note 2)	V <sub>SD</sub>	_	0.8	_	V	

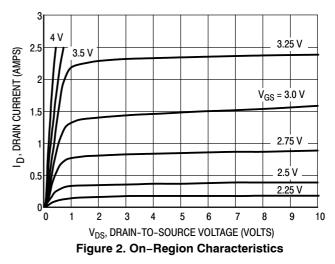
ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

2. Switching characteristics are independent of operating junction temperature.



### **TYPICAL ELECTRICAL CHARACTERISTICS**



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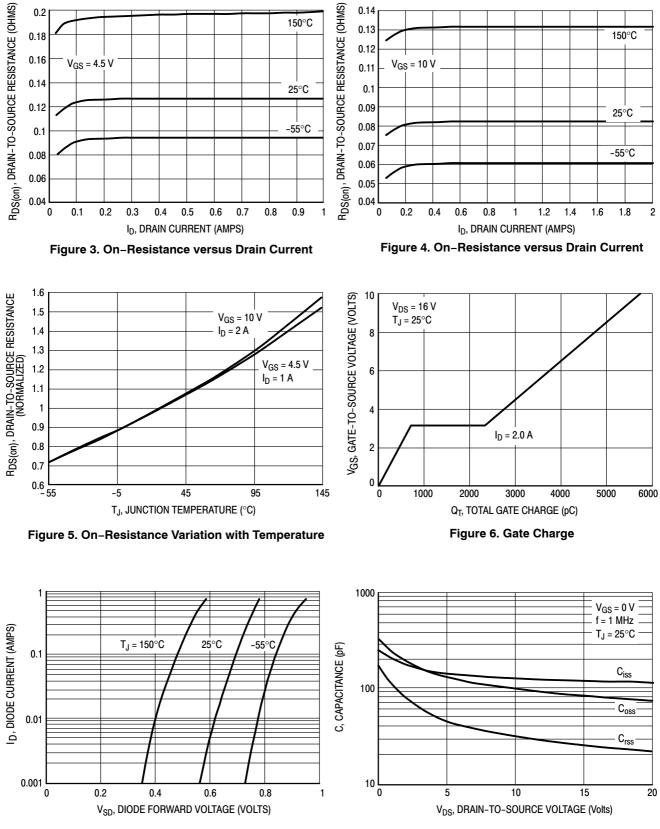


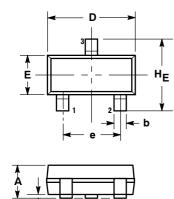
Figure 7. Body Diode Forward Voltage

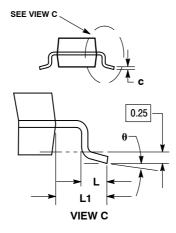
Figure 8. Capacitance

#### PACKAGE DIMENSIONS

#### SOT-23 (TO-236) CASE 318-08 ISSUE AP

NOTES





1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM

THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

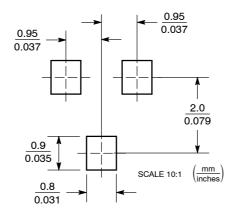
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR CALE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
Г	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
ΗE	2.10	2.40	2.64	0.083	0.094	0.104
A	٥°		100	٥°		10°

STYLE 21: PIN 1. GATE 2. SOURCE

3. DRAIN

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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